

10V Drive Nch MOSFET

R6015ANX

●Structure

Silicon N-channel MOSFET

●Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Gate-source voltage (V_{GS}) guaranteed to be $\pm 30V$.
- 4) Drive circuits can be simple.
- 5) Parallel use is easy.

●Applications

Switching

●Packaging specifications

Type	Package	Bulk
	Code	-
	Basic ordering unit (pieces)	500
R6015ANX		○

●Absolute maximum ratings ($T_a=25^\circ C$)

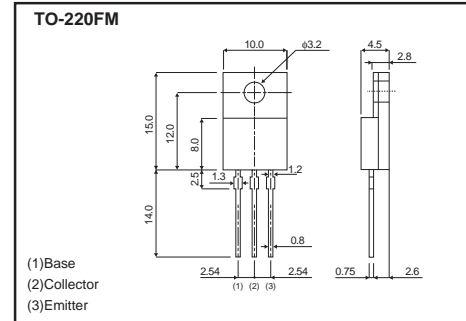
Parameter	Symbol	Limits	Unit	
Drain-source voltage	V_{DS}	600	V	
Gate-source voltage	V_{GS}	± 30	V	
Drain current	Continuous	I_D *3	± 15	A
	Pulsed	I_{DP} *1	± 60	A
Source current (Body Diode)	Continuous	I_S *3	15	A
	Pulsed	I_{SP} *1	60	A
Avalanche Current	I_{AS} *2	7.5	A	
Avalanche Energy	E_{AS} *2	15.0	mJ	
Total power dissipation ($T_C=25^\circ C$)	P_D	50	W	
Channel temperature	T_{ch}	150	$^\circ C$	
Range of storage temperature	T_{stg}	-55 to +150	$^\circ C$	

*1 $P_w \leq 10 \mu s$, Duty cycle $\leq 1\%$

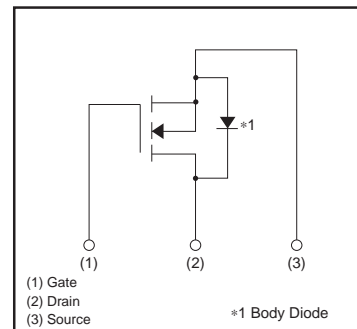
*2 $L = 500 \mu H$, $V_{DS} = 50V$, $R_G = 25 \Omega$, Starting, $T_{ch} = 25^\circ C$

*3 Limited only by maximum temperature allowed

●Dimensions (Unit : mm)



●Inner circuit



Transistors

● Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to case	Rth(ch-c)	2.5	°C/W

● Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	–	–	±100	nA	V _{GS} =±30V, V _{DS} =0V
Drain-source breakdown voltage	V _{(BR)DSS}	600	–	–	V	I _D =1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	–	–	100	μA	V _{DS} =600V, V _{GS} =0V
Gate threshold voltage	V _{GS(th)}	2.5	–	4.5	V	V _{DS} =10V, I _D =1mA
Static drain-source on-state resistance	R _{DS(on)} [*]	–	0.23	0.3	Ω	I _D =7.5A, V _{GS} =10V
Forward transfer admittance	Y _{fs} [*]	4.5	–	–	S	I _D =7.5A, V _{DS} =10V
Input capacitance	C _{iss}	–	1700	–	pF	V _{DS} =25V
Output capacitance	C _{oss}	–	1120	–	pF	V _{GS} =0V
Reverse transfer capacitance	C _{rss}	–	80	–	pF	f=1MHz
Turn-on delay time	t _{d(on)} [*]	–	50	–	ns	I _D =7.5A, V _{DD} ≒300V
Rise time	t _r [*]	–	50	–	ns	V _{GS} =10V
Turn-off delay time	t _{d(off)} [*]	–	150	–	ns	R _L =40Ω
Fall time	t _f [*]	–	60	–	ns	R _G =10Ω
Total gate charge	Q _g [*]	–	50	–	nC	V _{DD} ≒300V I _D =15A
Gate-source charge	Q _{gs} [*]	–	8	–	nC	V _{GS} =10V
Gate-drain charge	Q _{gd} [*]	–	20	–	nC	R _L =20Ω / R _G =10Ω

* Pulsed

● Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _{SD} [*]	–	–	1.5	V	I _S =15A, V _{GS} =0V

* Pulsed

Transistors

● Electrical characteristic curves

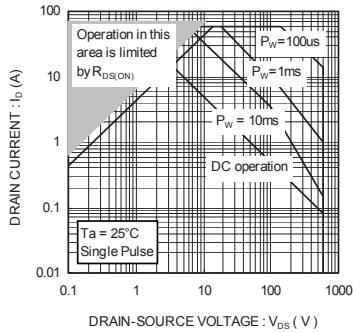


Fig.1 Maximum Safe Operating Area

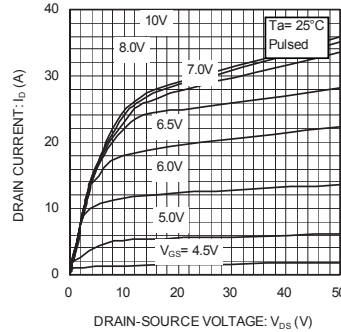


Fig.2: Typical Output Characteristics(I)

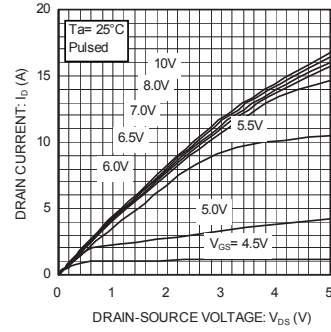


Fig.3: Typical Output Characteristics(II)

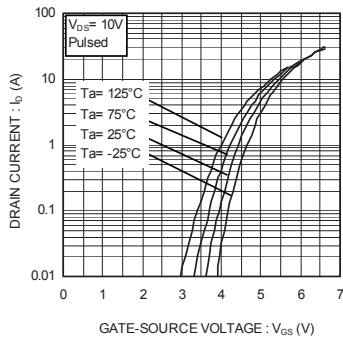


Fig.4 Typical Transfer Characteristics

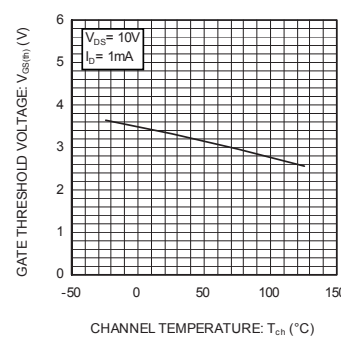


Fig.5 Gate Threshold Voltage vs. Channel Temperature

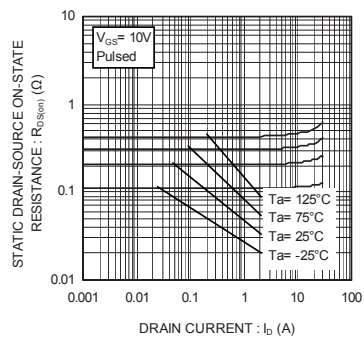


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current

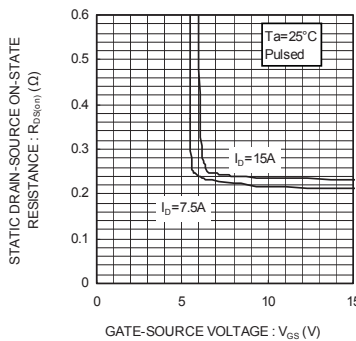


Fig.7 Static Drain-Source On-State Resistance vs. Gate Source Voltage

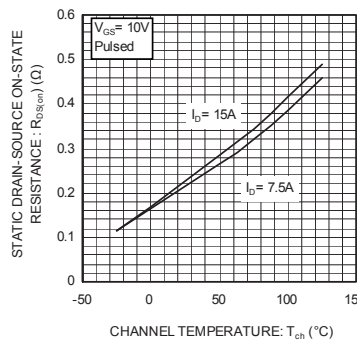


Fig.8 Static Drain-Source On-State Resistance vs. Channel Temperature

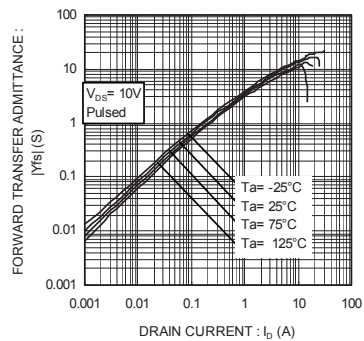


Fig.9 Forward Transfer Admittance vs. Drain Current

Transistors

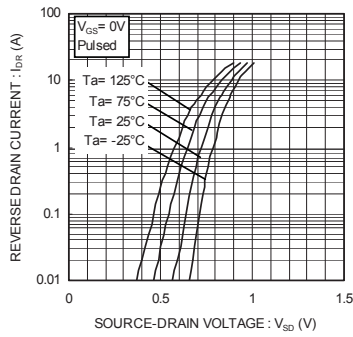


Fig.10 Reverse Drain Current vs. Source-Drain Voltage

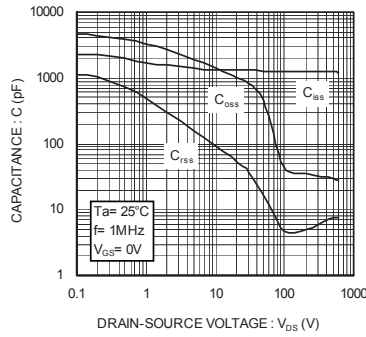


Fig.11 Typical Capacitance vs. Drain-Source Voltage

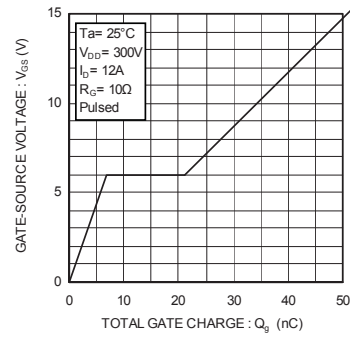


Fig.12 Dynamic Input Characteristics

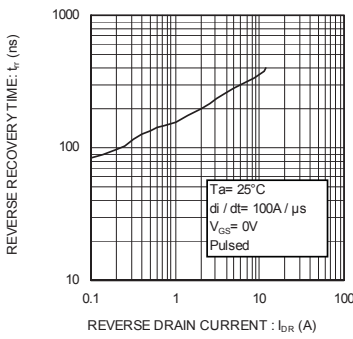


Fig.13 Reverse Recovery Time vs. Reverse Drain Current

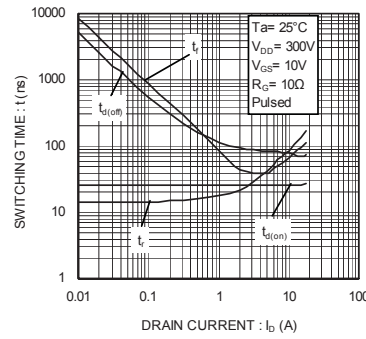


Fig.14 Switching Characteristics

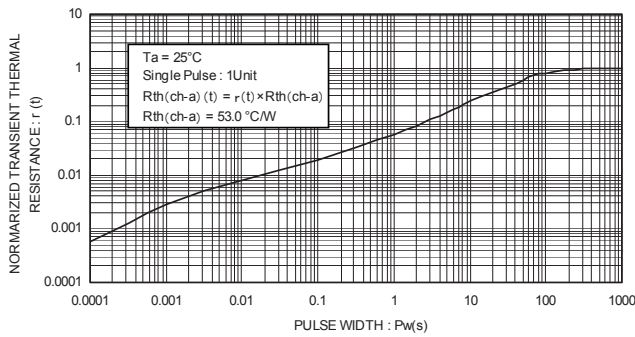


Fig.15 Normalized Transient Thermal Resistance vs. Pulse Width

Transistors

●Switching characteristics measurement circuit

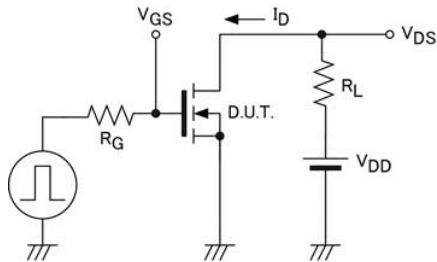


Fig.1-1 Switching Time Measurement Circuit

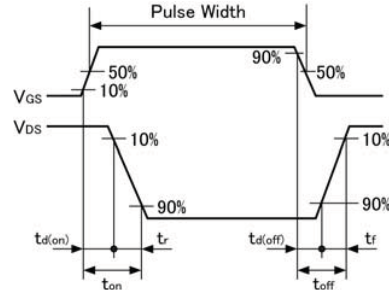


Fig.1-2 Switching Waveforms

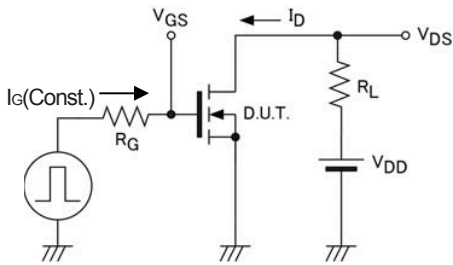


Fig.2-1 Gate Charge Measurement Circuit

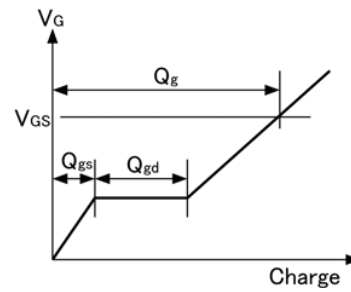


Fig.2-2 Gate Charge Waveform

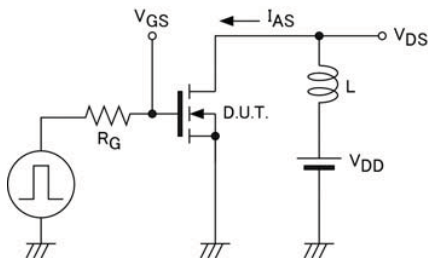


Fig.3-1 Avalanche Measurement Circuit

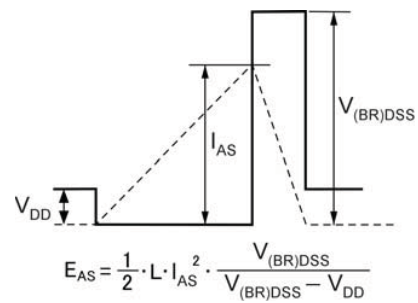


Fig.3-2 Avalanche Waveform

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